

PTO/SB/066 (07-09)

Approved for use through 07/31/2012 GRSB 0661-0031
U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no person is required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449/PTO		<i>Complete if Known</i>	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Application Number	10/563,105-Conf. #4561
(Use as many sheets as necessary)		Filing Date	December 30, 2005
		First Named Inventor	Misao TAKAKUSAKI
		Art Unit	1792
		Examiner Name	M. J. Song
Sheet	1	of	1
		Attorney Docket Number	1592-0158PUS1

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Column, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)	MM-DD-YYYY		

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear
		Causey Code ² -Number/Kind Code ² (if known)	MM-DD-YYYY		T ⁴

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue numbers, publisher, city and/or country where published.			T ⁴
	CA	MI et al., "Improvement of optical and electronic properties in broken gap mid-wave infrared laser materials," Conference on Lasers and Electro-Optics (CLEO 2001), Technical Digest, Postconference Edition, Baltimore, Md., May 6-11, 2001 [Trends in Optics and Photonics, (Top), US Washington, WA: OSA, US, Vol. 56, pp. 486-487, XP010560097]			
	CB	HARPER et al., "Cross-sectional scanning tunneling microscopy characterization of molecular beam epitaxy grown InAs/GaSb/AlSb heterostructures for mid-infrared interband cascade lasers," Journal of Vacuum Science & Technology B: Microelectronicsprocessing and Phenomena, American Vacuum Society, New York, NY, US, Vol. 16, No. 3, May 1, 1998, pg. 1389-1394, XP012006832			
	CC	HASENBERG et al., "Molecular beam epitaxy growth and characterization of broken-gap (type II) superlattices and quantum wells for midwave-infrared laser diodes," Journal of Vacuum Science & Technology B: Microelectronicsprocessing and Phenomena, American Vacuum Society, New York, NY, US, Vol. 18, No. 3, May 1, 2000, pp. 1623-1627, XP012006258			
	CD	DE SALVO et al., "Citric Acid Etching of Ga _{1-x} Sb _x , Al _{0.5} Ga _{0.5} Sb, and InAs for Heterostructure Device Fabrication," Journal of the Electrochemical Society, Electrochemical Society, Manchester, New Hampshire, US, Vol. 141, No. 12, December 1, 1994, pp. 3526-3531, XP000495786			

Examiner Signature	/Matthew Song/	Date Considered	02/11/2010

*EXAMINER: initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹Applicant's unique citation designation number (optional). ²See Kinds of References in USPTO Patent Documents at www.uspto.gov or MPEP 601.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.16). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶Applicant is to place a check mark here if English language translation is attached.